

PW3134KDW

20V Dual N-Channel MOSFET

0.75A 20V; $R_{DS(ON)typ}=190m\Omega@4V$, $R_{DS(ON)typ}=260m\Omega@2.5V$,
 $R_{DS(ON)typ}=390m\Omega@1.8V$.

FEATURE

- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

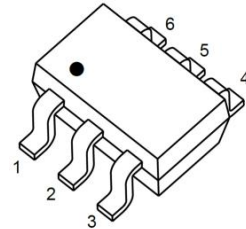
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

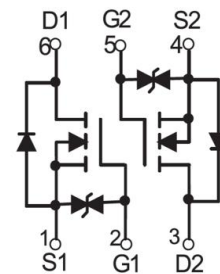
MARKING:



SOT-363



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

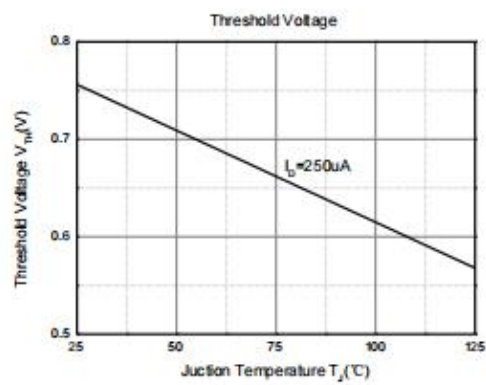
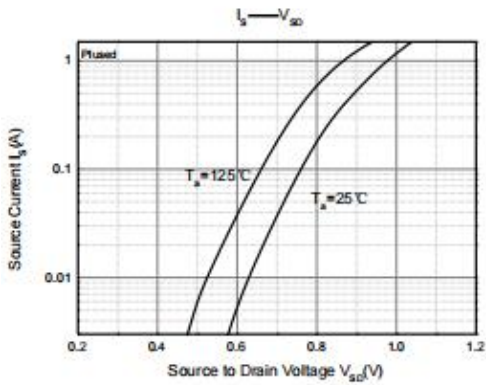
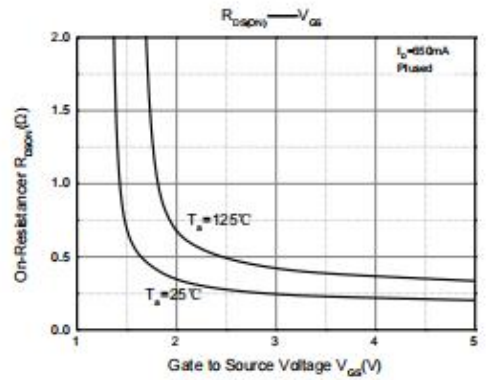
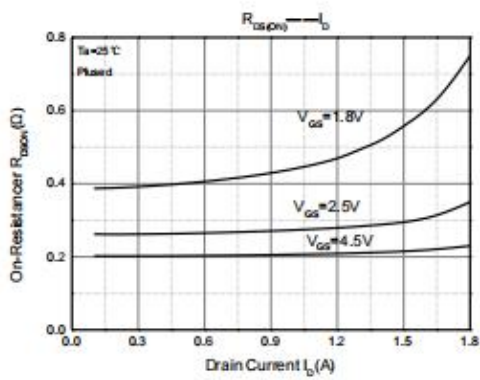
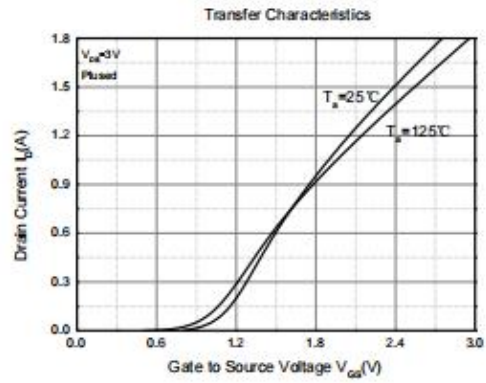
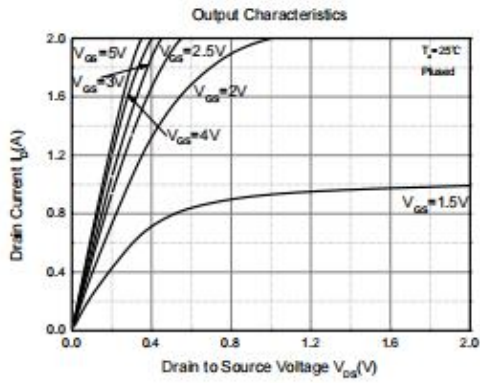
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ¹	I_D	0.75	A
Power Dissipation ¹	P_D	150	mW
Thermal Resistance from Junction to Ambient ¹	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

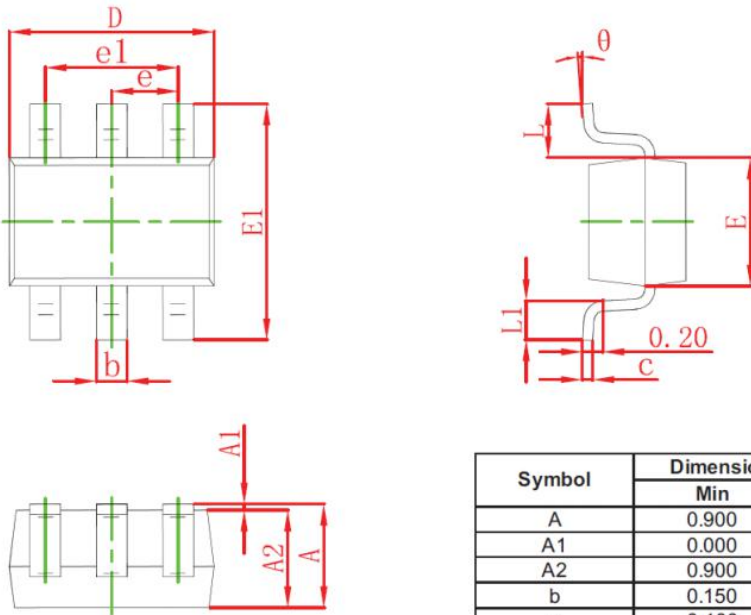
MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±20	uA
Gate threshold voltage ⁽¹⁾	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.35	0.75	1.1	V
Drain-source on-resistance ⁽¹⁾	R _{DS(on)}	V _{GS} = 4.5V, I _D = 650mA		190	260	mΩ
		V _{GS} = 2.5V, I _D = 550mA		260	360	
		V _{GS} = 1.8V, I _D = 450mA		390	590	
Forward tranconductance ⁽¹⁾	g _{FS}	V _{DS} = 10V, I _D = 800mA		1.6		S
DYNAMIC CHARACTERISTICS⁽²⁾						
Input Capacitance	C _{iss}	V _{DS} = 16V, V _{GS} = 0V, f = 1MHz			120	pF
Output Capacitance	C _{oss}				20	
Reverse Transfer Capacitance	C _{rss}				15	
SWITCHING CHARACTERISTICS⁽²⁾						
Turn-on delay time	t _{d(on)}	V _{DS} = 10V, I _D = 500mA, V _{GS} = 4.5V, R _G = 10Ω		6.7		nS
Turn-on rise time	t _r			4.8		
Turn-off delay time	t _{d(off)}			17.3		
Turn-off fall time	t _f			7.4		
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward voltage ⁽¹⁾	V _{DS}	I _S = 0.15A, V _{GS} = 0V			1.2	V

Notes :

1. Pulse Test : Pulse width ≤ 300 μ s, duty cycle ≤ 0.5%.
2. Guaranteed by design, not subject to production testing.

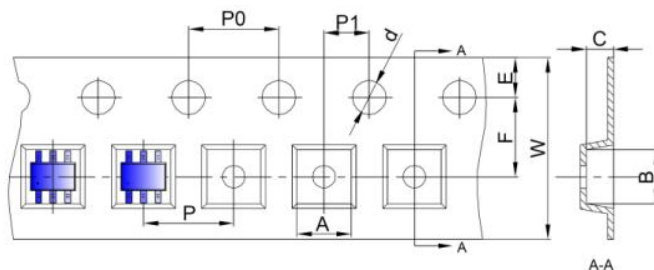




Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

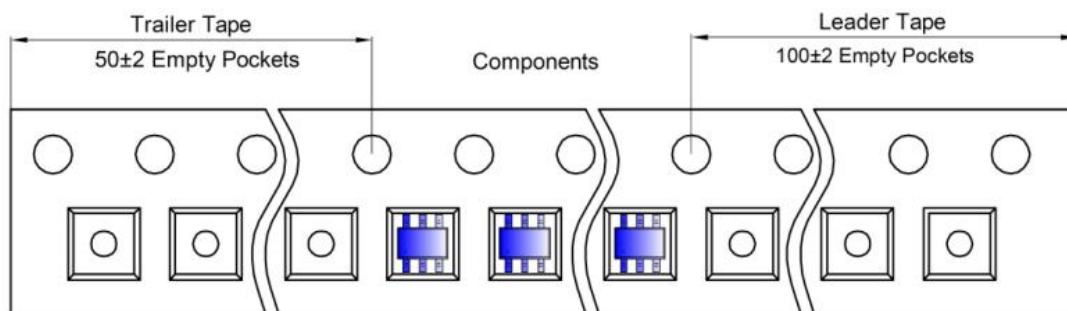
SOT-363 Tape and Reel

SOT-363 Embossed Carrier Tape

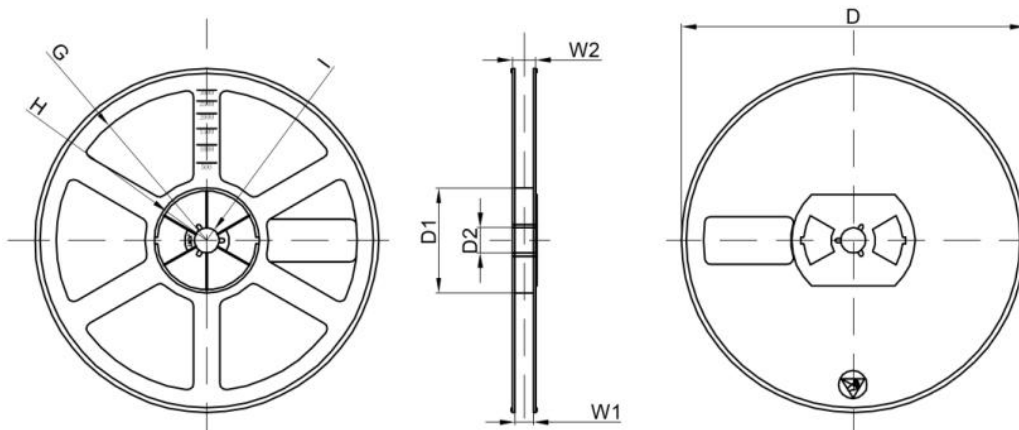


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-363	2.25	2.55	1.20	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-363 Tape Leader and Trailer



SOT-363 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	